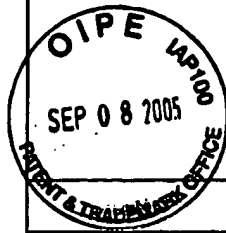


FORM PTO - 1449

## INFORMATION DISCLOSURE STATEMENT



ATTY DOCKET NO.: ASC-023C2

APPLICANTS: Fitzgerald

SERIAL NO.: 10/826,156

FILING DATE: April 16, 2004

GROUP: 2826

## U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
MLT	A1	2002/0100942	08/01/2001	Fitzgerald et al.			06/19/2001
	A2	2002/0084000	07/04/2002	Fitzgerald			12/17/2001
	A3	2002/0096717	07/25/2002	Chu et al.			01/25/2001
	A4	2002/0123197	09/05/2002	Fitzgerald et al.			06/19/2001
	A5	2002/0123183	09/05/2002	Fitzgerald			07/16/2001
	A6	2002/0123167	09/05/2002	Fitzgerald			07/16/2001
	A7	2002/0125497	09/12/2002	Fitzgerald			07/16/2001
	A8	2002/0125471	09/12/2002	Fitzgerald et al.			12/04/2001
	A9	2002/0168864	11/14/2002	Cheng et al.			
	A10	2003/0013323	01/16/2003	Hammond et al.			
	A11	2003/0025131	02/06/2003	Lee et al.			
	A12	2003/0034529	02/20/2003	Fitzgerald et al.			
	A13	2003/0057439	03/17/2003	Fitzgerald			
	A14	2003/0077867	04/24/2003	Fitzgerald			
	A15	2003/0102498	06/05/2003	Braithwaite et al.			
	A16	2003/0227057	12/11/2003	Lochtefeld et al.			10/04/2002
	A17	2004/0005740	01/08/2004	Lochtefeld et al.			06/06/2003
	A18	2004/0031979	02/19/2004	Lochtefeld et al.			06/06/2003
	A19	2004/0075149	04/22/2004	Fitzgerald et al.			07/23/2003
	A20	2004/0219726	11/04/2004	Fitzgerald			05/26/2004
	A21	2004/0262631	12/13/2004	Fitzgerald			04/16/2004
	A22	2005/0009288	01/13/2005	Cheng et al.			03/17/2004
	A23	2005/0156246	07/21/2005	Langdo et al.			03/07/2005
	A24	4,010,045	03/01/1977	Ruehrwein			
	A25	4,710,788	12/01/1987	Dambkes et al.			
	A26	4,900,372	12/13/1990	Lee et al.			
	A27	4,987,462	01/22/1991	Kim et al.			
	A28	4,990,979	02/05/1991	Otto			
	A29	4,997,776	03/05/1991	Haramé et al.			
	A30	5,013,681	05/07/1991	Godbey et al.			
MLT	A31	5,091,767	02/25/1992	Bean et al.			

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				<b>SERIAL NO.: 10/826,156</b>			
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<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
MLT	A32	5,097,630	03/24/1992	Maeda <i>et al.</i>			
	A33	5,155,571	10/13/1992	Wang <i>et al.</i>			
	A34	5,159,413	10/27/1992	Calviello <i>et al.</i>			
	A35	5,166,084	11/24/1992	Pfiester			
	A36	5,177,583	01/05/1993	Endo <i>et al.</i>			
	A37	5,202,284	04/01/1993	Kamins <i>et al.</i>			
	A38	5,207,864	05/04/1993	Bhat <i>et al.</i>			
	A39	5,208,182	05/04/1993	Narayan <i>et al.</i>			
	A40	5,210,052	05/11/1993	Takasaki			
	A41	5,212,110	05/18/1993	Pfiester <i>et al.</i>			
	A42	5,221,413	06/22/1993	Brasen <i>et al.</i>			
	A43	5,241,197	08/31/1993	Murakami <i>et al.</i>			
	A44	5,250,445	10/05/1993	Bean <i>et al.</i>			
	A45	5,252,173	10/12/1993	Inoue			
	A46	5,279,687	01/18/1994	Tuppen <i>et al.</i>			
	A47	5,285,086	02/08/1994	Fitzgerald, Jr.			
	A48	5,291,439	03/01/1994	Kauffmann, <i>et al.</i>			
	A49	5,298,452	03/29/1994	Meyerson			
	A50	5,308,444	05/03/1994	Fitzgerald <i>et al.</i>			
	A51	5,310,451	05/10/1994	Tejwani <i>et al.</i>			
	A52	5,316,958	05/31/1994	Meyerson			
	A53	5,346,848	09/13/1994	Gruppen-Shemansky <i>et al.</i>			
	A54	5,374,564	12/20/1994	Bruel			
	A55	5,413,679	05/09/1995	Godbey			
	A56	5,424,243	06/13/1995	Takasaki			
	A57	5,425,846	06/20/1995	Koze <i>et al.</i>			
	A58	5,426,069	06/20/1995	Selvakumar <i>et al.</i>			
	A59	5,426,316	06/20/1995	Mohammad			
	A60	5,461,243	10/24/1995	Ek <i>et al.</i>			
	A61	5,461,250	10/24/1995	Burghartz <i>et al.</i>			
MLT	A62	5,462,883	10/31/1995	Dennard <i>et al.</i>			
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<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
MLT	A63	5,476,813	12/19/1995	Naruse			
	A64	5,479,033	12/26/1995	Baca et al.			
	A65	5,484,664	01/16/1996	Kitahara et al.			
	A66	5,523,243	06/04/1996	Mohammad			
	A67	5,523,592	06/04/1996	Nakagawa et al.			
	A68	5,534,713	07/09/1996	Ismail et al.			
	A69	5,536,361	07/16/1996	Kondo et al.			
	A70	5,540,785	07/30/1996	Dennard et al.			
	A71	5,596,527	01/12/1997	Tomioka, et al.			
	A72	5,617,351	04/01/1997	Bertin, et al.			
	A73	5,630,905	05/20/1997	Lynch et al.			
	A74	5,633,516	05/27/1997	Mishima et al.			
	A75	5,659,187	08/19/1997	Legoues et al.			
	A76	5,683,934	11/04/1997	Candelaria			
	A77	5,698,869	12/16/1997	Yoshimi et al.			
	A78	5,714,777	02/03/1998	Ismail et al.			
	A79	5,728,623	03/17/1998	Mori			
	A80	5,739,567	04/14/1998	Wong			
	A81	5,759,898	06/02/1998	Ek et al.			
	A82	5,777,347	07/07/1998	Bartelink			
	A83	5,786,612	07/28/1998	Otani et al.			
	A84	5,786,614	07/28/1998	Chuang, et al.			
	A85	5,792,679	08/11/1998	Nakato			
	A86	5,801,085	09/01/1998	Kim et al.			
	A87	5,808,344	09/15/1998	Ismail et al.			
	A88	5,810,924	09/22/1998	Legoues et al.			
	A89	5,828,114	10/27/1998	Kim et al.			
	A90	5,847,419	12/08/1998	Imai et al.			
	A91	5,859,864	01/12/1999	Jewell			
	A92	5,877,070	03/02/1999	Goesele et al.			
MLT	A93	5,891,769	04/06/1999	Liaw et al.			
<b>EXAMINER</b> Minhloan Tran				<b>DATE CONSIDERED</b> 11/05			

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<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
MLT	A94	5,906,708	05/25/1999	Robinson et al.			
	A95	5,906,951	05/25/1999	Chu et al.			
	A96	5,912,479	06/15/1999	Mori et al.			
	A97	5,943,560	08/24/1999	Chang et al.			
	A98	5,963,817	10/05/1999	Chu et al.			
	A99	5,966,622	10/12/1999	Levine et al.			
	A100	5,998,807	12/07/1999	Lustig et al.			
	A101	6,010,937	01/04/2000	Karam et al.			
	A102	6,013,134	01/11/2000	Chu et al.			
	A103	6,030,884	02/29/2000	Mori			
	A104	6,033,974	03/07/2000	Henley et al.			
	A105	6,033,995	03/07/2000	Muller			
	A106	6,039,803	03/21/2000	Fitzgerald et al.			
	A107	6,058,044	05/02/2000	Sugiura et al.			
	A108	6,059,895	05/09/2000	Chu et al.			
	A109	6,074,919	06/13/2000	Gardner et al.			
	A110	6,096,590	08/01/2000	Chan et al.			
	A111	6,103,559	08/15/2000	Gardner et al.			
	A112	6,107,653	08/22/2000	Fitzgerald			
	A113	6,111,267	08/29/2000	Fischer et al.			
	A114	6,117,750	09/12/2000	Bensahel et al.			
	A115	6,124,614	09/26/2000	Ryum et al.			
	A116	6,130,453	10/10/2000	Mei, et al.			
	A117	6,133,799	10/17/2000	Favors, Jr., et al.			
	A118	6,140,687	10/31/2000	Shimomura et al.			
	A119	6,143,636	11/07/2000	Forbes, et al.			
	A120	6,153,495	11/28/2000	Kub et al.			
	A121	6,154,475	11/28/2000	Soref et al.			
	A122	6,160,303	12/12/2000	Fattaruso			
	A123	6,162,688	12/19/2000	Gardner et al.			
MLT	A124	6,184,111	02/06/2001	Henley et al.			
<b>EXAMINER</b> Minhloan Tran				<b>DATE CONSIDERED</b> 11/05			

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<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
MLT	A125	6,191,006	02/20/2001	Mori			
	A126	6,191,007	02/20/2001	Matsui et al.			
	A127	6,191,432	02/20/2001	Sugiyama et al.			
	A128	6,194,722	02/27/2001	Fiorini et al.			
	A129	6,204,529	03/20/2001	Lung, et al.			
	A130	6,207,977	03/01/2001	Augusto			
	A131	6,210,988	04/03/2001	Howe et al.			
	A132	6,218,677	04/17/2001	Broekaert			
	A133	6,232,138	05/15/2001	Fitzgerald et al.			
	A134	6,235,567	05/22/2001	Huang			
	A135	6,242,324	06/05/2001	Kub et al.			
	A136	6,249,022	06/19/2001	Lin, et al.			
	A137	6,251,755	06/26/2001	Furukawa et al.			
	A138	6,261,929	07/01/2001	Gehrke et al.			
	A139	6,271,551	08/07/2001	Schmitz et al.			
	A140	6,271,726	08/07/2001	Fransis et al.			
	A141	6,291,321	09/18/2001	Fitzgerald			
	A142	6,313,016	11/06/2001	Kibbel et al.			
	A143	6,316,301	11/13/2001	Kant			
	A144	6,323,108	11/27/2001	Kub et al.			
	A145	6,329,063	12/11/2001	Lo et al.			
	A146	6,335,546	01/01/2002	Tsuda et al.			07/30/1999
	A147	6,350,993	02/26/2002	Chu et al.			
	A148	6,368,733	04/09/2002	Nishinaga			08/05/1999
	A149	6,372,356	04/16/2002	Thornton et al.			04/028/2000
	A150	6,399,970	06/04/2002	Kubo et al.			09/16/1997
	A151	6,403,975	06/11/2002	Brunner et al.			
	A152	6,406,589	06/18/2002	Yanagisawa			
	A153	6,407,406	06/18/2002	Tezuka			06/29/1999
	A154	6,425,951	07/30/2002	Chu et al.			08/06/1999
MLT	A155	6,429,061	08/06/2002	Rim			07/26/2000
EXAMINER <i>Minhloan Tran</i>				DATE CONSIDERED <i>11/05</i>			

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<b>INFORMATION DISCLOSURE STATEMENT</b>				<b>APPLICANTS: Fitzgerald</b>			
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<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
MLT	A156	6,521,041	02/18/2003	Wu et al.			04/09/1999
	A157	6,521,041	02/18/2003	Wu et al.			04/09/1999
	A158	6,555,839	04/29/2003	Fitzgerald			05/16/2001
	A159	6,573,126	06/03/2003	Cheng et al.			08/10/2001
	A160	6,583,015	06/24/2003	Fitzgerald et al.			08/06/2001
	A161	6,593,191	07/15/2003	Fitzgerald			05/16/2001
	A162	6,602,613	08/05/2003	Fitzgerald			
	A163	6,646,322	11/11/2003	Fitzgerald			07/16/2001
	A164	6,649,480	11/18/2003	Fitzgerald et al.			06/19/2001
	A165	6,677,192	01/13/2004	Fitzgerald			07/16/2001
	A166	6,703,144	03/09/2004	Fitzgerald			03/18/2003
	A167	6,703,688	03/09/2004	Fitzgerald			07/16/2001
	A168	6,723,661	04/20/2004	Fitzgerald			07/16/2001
	A169	6,724,008	04/20/2004	Fitzgerald			07/16/2001
	A170	6,730,551	05/04/2004	Lee et al.			08/02/2002
	A171	6,750,130	06/15/2004	Fitzgerald			01/07/2001
	A172	6,830,976	12/14/2004	Fitzgerald			07/16/2001
	A173	6,876,010	04/05/2005	Fitzgerald			06/07/2000
MLT	A174	6,881,632	04/19/2005	Fitzgerald et al.			07/01/2000
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<b>FOREIGN PATENT DOCUMENTS</b>									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
MLT	B1	2001-319935	11/16/2001	JP				N	Y
	B2	4-307974	10/30/1992	JP				N	N
	B3	10-270685	10/09/1998	JP				N	Y
	B4	6-252046	11/19/1992	JP				N	Y
	B5	7-240372	09/12/1995	JP				NO	Abstract
	B6	11-233744	08/27/1999	JP				N	N
	B7	2-210816	08/22/1990	JP				N	Abstract
	B8	6-177046	06/24/1994	JP				N	Abstract
	B9	5-166724	07/02/1993	JP				N	Abstract
	B10	61-141116	06/28/1996	JP				N	Abstract
	B11	7-106446	04/21/1995	JP				N	N
	B12	3-36717	02/18/1991	JP				N	Abstract
	B13	2000-031491	01/28/2000	JP				N	N
	B14	2000-021783	08/31/2000	JP				N	Y
	B15	00/48239	08/17/2000	WO				N	Y
	B16	00/54338	09/14/2000	WO				N	Y
	B17	98/59365	12/30/1998	WO				N	Y
	B18	99/53539	10/21/1999	WO				N	Y
	B19	41 01 167	07/23/1992	DE				N	N
	B20	1 020 900	07/19/2000	EP				N	Y
	B21	1 174 928	01/23/2002	EP				N	Y
	B22	0 587 520	03/16/1994	EP				N	Y
	B23	2 342 777	04/19/2000	GB				Y	Y
	B24	0 828 296	03/11/1998	EP				N	Y
	B25	0 683 522	11/22/1995	EP				N	Y
	B26	0 838 858	04/29/1998	EP				N	N
	B27	0 829 908	03/18/1998	EP				N	Y
	B28	63-73398	04/02/1988	JP				N	N
	B29	6-244112	09/02/1994	JP				N	N
MLT	B30	7-094420	04/07/1995	JP				N	Abstract
<b>EXAMINER</b> Minhloan Tran					<b>DATE CONSIDERED</b> 11/05				

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		<b>SERIAL NO.:</b> 10/826,156	
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		<b>GROUP:</b> 2826	
<b>OTHER ART, JOURNAL ARTICLES, ETC.</b>			
<b>EXAM. INIT.</b>	<b>OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)</b>		
MLT	C1	Armstrong et al., "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," IEDM Technical Digest (1995 International Electron Devices Meeting) pp. 761-764.	
	C2	Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices", PhD Thesis, Massachusetts Institute of Technology, 1999, pp. 1-154.	
	C3	Augusto et al., "Proposal for a New Process Flow for the Fabrication of Silicon-based Complementary MOD-MOSFETs without ion Implantation," Thin Solid Films, vol. 294, no. 1-2, pp. 254-258 (February 15, 1997).	
	C4	Borenstein et al., "A New Ultra-Hard Etch-Stop Layer for High Precision Micromachining," Proceedings of the 1999 12th IEEE International Conference on Micro Electro Mechanical Systems (MEMS) (January 17-21, 1999) pp. 205-210.	
	C5	Bouillon et al., "Search for the optimal channel architecture for 0.18/0.12 $\mu$ m bulk CMOS Experimental study," IEEE, (1996) pp. 21.2.1-21.2.4.	
	C6	Bruehl et al., "SMART CUT: A Promising New SOI Material Technology," Proceedings 1995 IEEE International SOI Conference (October 1995) pp. 178-179.	
	C7	Bruehl, "Silicon on Insulator Material Technology," Electronic Letters, Vol. 13, No. 14 (July 6, 1995) pp. 1201-1202.	
	C8	Bufler et al., "Hole transport in strained Si <sub>1-x</sub> Ge <sub>x</sub> alloys on Si <sub>1-y</sub> Ge <sub>y</sub> substrates," Journal of Applied Physics, Vol. 84, No. 10 (November 15, 1998) pp. 5597-5602.	
	C9	Bulsara et al., "Relaxed In <sub>x</sub> Ga <sub>1-x</sub> As Graded Buffers Grown with Organometallic Vapor Phase Epitaxy on GaAs," <u>Applied Physics Letters</u> , Vol. 72, Issue 13 (July 30, 1998), pp. 1608-1610.	
	C10	Bulsara, "Materials Issues with the Integration of Lattice-Mismatched In <sub>x</sub> Ga <sub>1-x</sub> As on GaAs," PhD Thesis, MIT, June 1998, pp. 1-178.	
	C11	Burghartz et al., "Microwave Inductors and Capacitors in Standard Multilevel Interconnect Silicon Technology", IEEE Transactions on Microwave Theory and Techniques, Vol. 44, No. 1, January 1996, pp. 100-104.	
	C12	Carlin et al., "High Efficiency GaAs-on-Si Solar Cells with High Voc Using Graded GeSi Buffers," IEEE (2000) pp. 1006-1011	
	C13	Chang et al., "Selective Etching of SiGe/Si Heterostructures," Journal of the Electrochemical Society, No. 1 (January 1991) pp. 202-204.	
	C14	Charasse et al., "MBE Growth of GaAs on Si at Thomson," <u>Institute of Electronic Structure and Laser</u>	
	C15	Crumbaker et al., "The Influence of Dislocation Density on Electron Mobility in InP Films on Si," <u>Applied Physics Letters</u> , Vol. 59, Issue 9 (08/26/91), pp. 1090-1092.	
MLT	C16	Cullis et al., "Growth ripples upon strained SiGe epitaxial layers on Si and misfit dislocation interactions," Journal of Vacuum Science and Technology A, Vol. 12, No. 4 (July/August 1994) pp. 1924-1931.	
<b>EXAMINER</b> Minhloan Tran		<b>DATE CONSIDERED</b> 11/05	



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<b>OTHER ART, JOURNAL ARTICLES, ETC.</b>			
<b>EXAM. INIT.</b>	<b>OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)</b>		
MLT	C17	Currie et al. "Controlling Threading Dislocation in Ge on Si Using Graded SiGe Layers and Chemical-Mechanical Polishing" vol. 72 No. 14 (Feb. 1998) pp. 1718-1720.	
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